





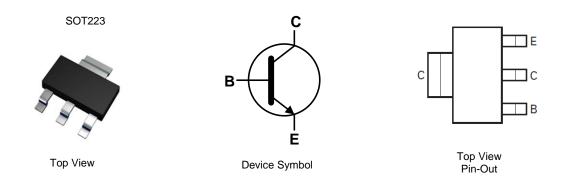
25V NPN HIGH CURRENT TRANSISTOR IN SOT223

Features

- BV_{CEO} > 25V
- I_C = 7A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Very Low Saturation Voltage V_{CE(sat)} < 110mV @ 1A
- R_{CE(sat)} = 36mΩ at 5A for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 20A for a High Gain Hold Up
- Ptot = 3W
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)



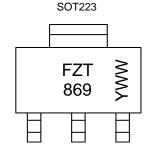
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT869TA	AEC-Q101	FZT869	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 869 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	7	Α
Peak Pulse Current	I _{CM}	20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3 24	W	
Linear Derating Factor	(Note 6)	- P _D	1.6 12.8	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ heta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	$R_{ heta JL}$	8.8		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

^{5.} For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.

^{6.} Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.

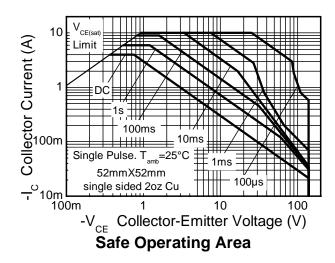
^{7.} Thermal resistance from junction to solder-point (at the end of the collector lead).

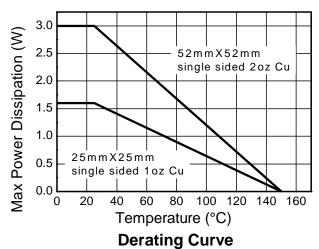
^{8.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.

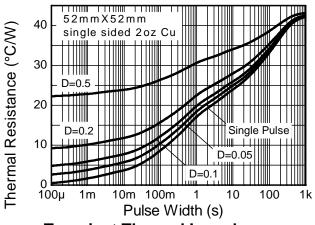


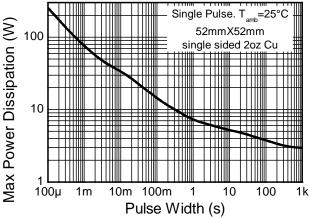


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

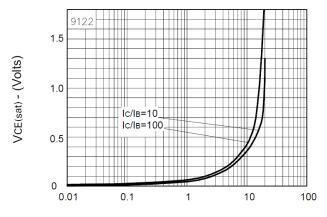
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	60	120	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	60	120	-	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	25	35	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	8	_	V	$I_{E} = 100 \mu A$
Collector Cut-off Current	Ісво	_ _	_ _	50 1	nΑ μΑ	V _{CB} = 50V V _{CB} = 50V, T _A = +100°C
Collector Cut-off Current	ICER	_ _	_ _	50 1	nΑ μΑ	$V_{CB} = 50V$, $R_B \le 1k\Omega$ $V_{CB} = 50V$, $T_A = +100$ °C
Emitter Cut-off Current	I _{EBO}	_	_	10	nA	V _{EB} = 6V
	h _{FE}	300	450	_	Г	I _C = 10mA, V _{CE} = 1V
DC Current Coin (Note 0)		300	450	-		$I_C = 1A$, $V_{CE} = 1V$
DC Current Gain (Note 9)		200	300	_		I _C = 7A, V _{CE} = 1V
		40	100	_		I _C = 20A, V _{CE} = 2V
	VCE(sat)	_	35	50	mV	$I_C = 0.5 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	67	110		I _C = 1A, I _B = 10mA
Collector-Emilier Saturation voltage (Note 9)		_	168	215	IIIV	$I_C = 2A, I_B = 10mA$
		_	_	350		$I_C = 6.5A$, $I_B = 150mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	_	1.2	V	$I_C = 6.5A$, $I_B = 300mA$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	_	_	1.13	mV	$I_C = 6.5A, V_{CE} = 1V$
Current Gain-Bandwidth Product (Note 9)	f _T	-	100	-	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Output Capacitance (Note 9)	C_{obo}	_	70		рF	$V_{CB} = 10V$, $f = 1MHz$
Switching Times	t _{on}	_	60		ns	$I_C = 1A, V_{CC} = 10V,$
Switching filles	t _{off}	_	680	_	115	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



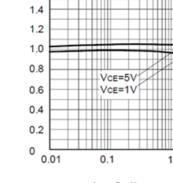
100

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



Ic - Collector Current (Amps)

VCE(sat) V IC

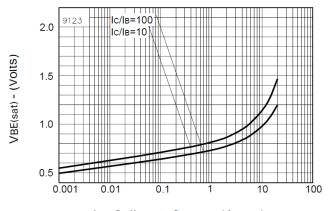


1.6

hre - Normalised Gain

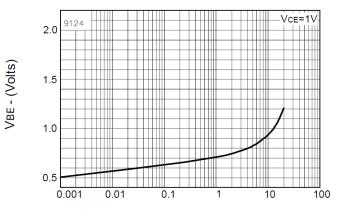
Ic - Collector Current (Amps)

hFE v IC



Ic - Collector Current (Amps)

VBE(sat) v IC



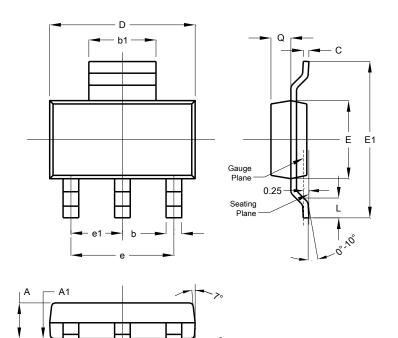
Ic - Collector Current (Amps)

VBE(on) V IC



Package Outline Dimensions

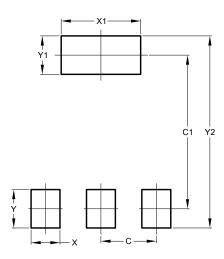
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)				
С	2.30				
C1	6.40				
Х	1.20				
X1	3.30				
Y	1.60				
Y1	1.60				
Y2	8.00				

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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